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<u>Diodes Incorporated</u> <u>ZXMP6A17GTA</u>

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Datasheet of ZXMP6A17GTA - MOSFET P-CH 60V 3A SOT223

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ZXMP6A17G

#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

# **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-60V	$125 m\Omega$ @ $V_{GS}$ = - $10V$	-4.3A
-60 <i>V</i>	190mΩ @ V <sub>GS</sub> = -4.5V	-3.5A

### Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

### **Features and Benefits**

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

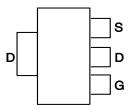
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

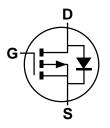
#### SOT223



Top View



Pin Out - Top View



**Equivalent Circuit** 

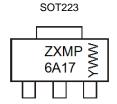
### Ordering Information (Note 4)

Proceedings of the control of the co		
Part Number	Case	Packaging
ZXMP6A17GTA	SOT223	1,000/Tape & Reel
ZXMP6A17GTC	SOT223	4,000/ Tape & Reel

Note:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



 $\begin{array}{l} ZXMP6A17 = Product\ Type\ Marking\ Code \\ YWW = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ 5=2015) \\ WW\ or\ \overline{W}W = Week\ (01-53) \\ \end{array}$ 



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# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	-60	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
		(Note 6)		-4.3	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	I <sub>D</sub>	-3.5	Α
		(Note 5)		-3.0	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 7)	I <sub>DM</sub>	-13.7	Α
Continuous Source Current (Body Diode) (Note		(Note 6)	I <sub>S</sub>	-4.8	Α
Pulsed Source Current (Body Diode) (Note 7)		I <sub>SM</sub>	-13.7	А	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	Б	2.0 16	W	
Linear Derating Factor	(Note 6)	PD	3.9 31	mW/°C	
The court Desistance of the first Auditor	(Note 5)	Б	62.5		
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	32.0	°C/W	
Thermal Resistance, Junction to Lead	(Note 8)	$R_{ heta JL}$	9.8		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### Notes:

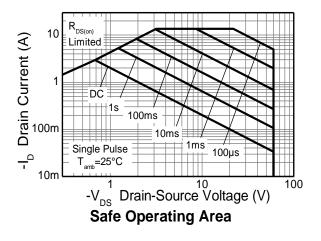
- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is measured at t ≤ 10sec.
  7. Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
  8. Thermal resistance from junction to solder-point (at the end of the drain lead).

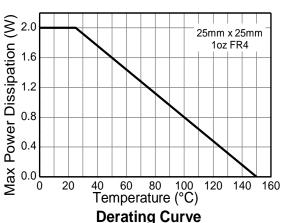


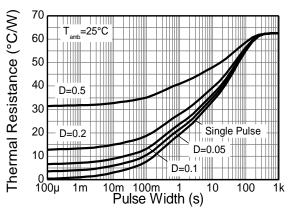


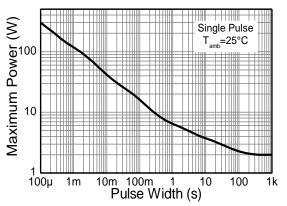
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### **Thermal Characteristics**









**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



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# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS	•		•	•	•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -60V, V_{G}$	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS	•		•	•	•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	_	_	V	$I_D = -250 \mu A, V_D$	$v_S = V_{GS}$	
Chatia Dania Causaa On Basistanaa (Nata O)	Б		0.096	0.125	0	V <sub>GS</sub> = -10V, I <sub>D</sub> :	= -2.2A	
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(ON)</sub>		0.120	0.190	Ω	$V_{GS} = -4.5V, I_{D}$	= -1.8A	
Forward Transconductance (Notes 9 & 10)	9 <sub>fs</sub>	_	4.7	_	S	$V_{DS} = -15V, I_{D} = -2.2A$		
Diode Forward Voltage (Note 9)	V <sub>SD</sub>	_	-0.85	-0.95	V	I <sub>S</sub> = -2.0A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C		
Reverse Recovery Time (Note 10)	t <sub>rr</sub>		25.1	_	ns	$I_S = -1.7A$ , di/dt = 100A/ $\mu$ s, $T_J = +25$ °C		
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	_	27.2		nC			
DYNAMIC CHARACTERISTICS (Note 10)								
Input Capacitance	C <sub>iss</sub>	_	637	_	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V -f = 1MHz		
Output Capacitance	Coss	_	70.0	_	pF			
Reverse Transfer Capacitance	C <sub>rss</sub>	_	53.0	_	pF			
Total Gate Charge (Note 11)	Qg	_	9.0	_	nC	$V_{GS} = -4.5V$		
Total Gate Charge (Note 11)	Qg	_	17.7	_	nC		V <sub>DS</sub> = -30V	
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	_	1.6		nC	V <sub>GS</sub> = -10V		
Gate-Drain Charge (Note 11)	Q <sub>gd</sub>	_	4.4		nC			
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>		2.6		ns	$V_{DD} = -30V, V_{GS} = -10V$ $I_{D} = -1A, R_{G} \cong 6.0\Omega$		
Turn-On Rise Time (Note 11)	t <sub>r</sub>	_	3.4	_	ns			
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	_	26.2	_	ns			
Turn-Off Fall Time (Note 11)	t <sub>f</sub>		11.3		ns	1		

Notes:

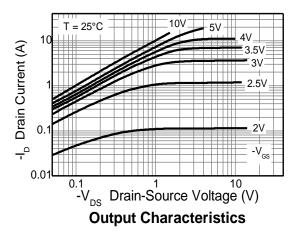
- 9. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq 2\%.$
- 10. For design aid only, not subject to production testing.
  11. Switching characteristics are independent of operating junction temperatures.

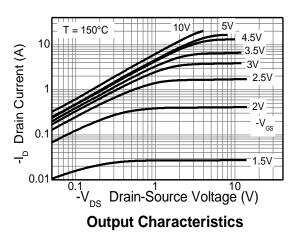


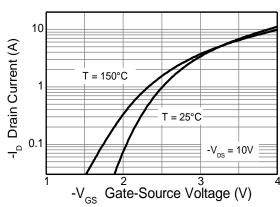


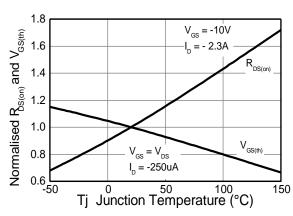
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# **Typical Characteristics**



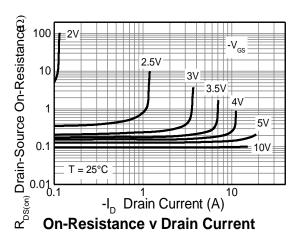


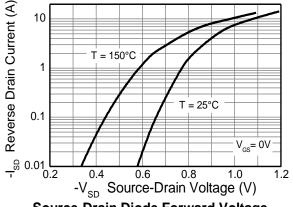




**Typical Transfer Characteristics** 





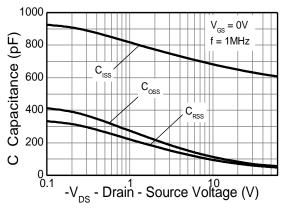


Source-Drain Diode Forward Voltage

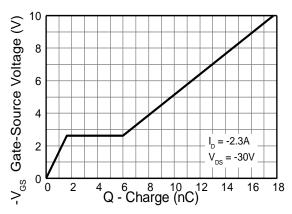


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### **Typical Characteristics** (cont.)

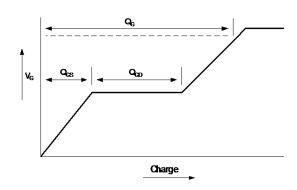


Capacitance v Drain-Source Voltage

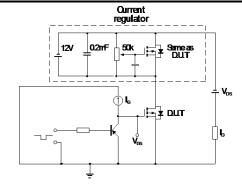


**Gate-Source Voltage v Gate Charge** 

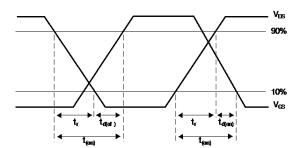
### **Test Circuits**



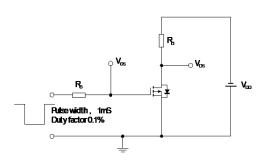
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

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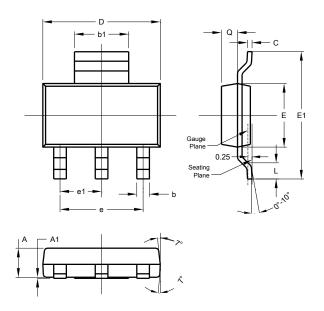
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# **Package Outline Dimensions**

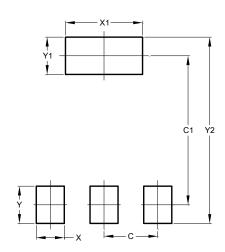
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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